1200V 18A N-Channel SiC MOSFET

Features

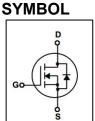
- Low On-Resistance
- Low Capacitance
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

BENEFITS

- Higher System Efficiency
- Parallel Device Convenience
- High Temperature Application
- High Frequency Operation

Application

- Switch Mode Power Supply (SMPS)
- Power Factor Correction (PFC)
- Uninterruptible Power Supply (UPS)
- EV Charging station & Motor Drives
- Solar/ Wind Renewable Energy
- Power Inverters & DC/DC Converters





TO-247

ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXW18M1K2H	TO-247	Tube

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter		Symbol	Rating	Unit
			TO-247	
Drain-Source Voltage		V _{DSS}	1200	V
Continuous Drain Current	T _C = 25°C, VGS=20V	lo	18	A
Single Pulse Avalanche Energy	L=10mH	E _{AS}	145	mJ
	L=10mH	las	5.4	A
Pulsed Drain Current		Ідм	72	A
Recommend Gate Source Voltage(Static)		V _{GS} ,op	-3/+20	V
Maximum Gate Source Voltage(AC (f > 1Hz))		V _{GS} ,max	-5/+25	V
Power Dissipation	Tc=25°C	PD	96.9	W
Soldering Temperature		TL	260	°C
Operating Junction and Storage Temperature Range		TJ,TSTG	150,-55~150	°C
Thermal Resistance, Junction to Case		RθJC	1.29	°C / W



BXW18M1K2H

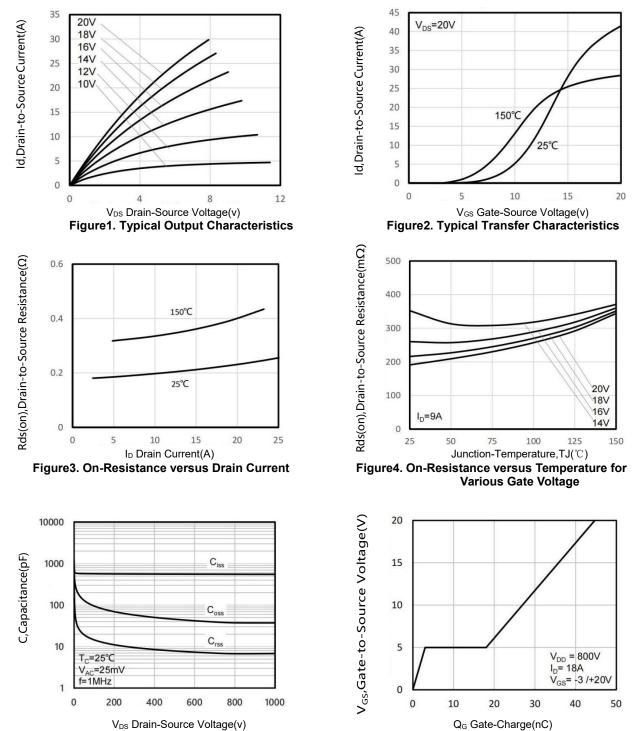
ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V, ID=250µA	1200			V
Zero Gate Voltage Drain Current	IDSS	VDS=1200V, VGS=0V			10	uA
Gate-Body Leakage Current, Forward	I _{GSS}	VGS=20V,VDS = 0V			250	nA
ON CHARACTERISTICS	-1				1	1
Gate Threshold Voltage	V _{GS(TH)}	VDS=VGS, ID=5mA	2.0		4.5	V
		VGS=20V, ID=9A		190	228	mΩ
		VGS=18V, ID=9A		215	258	
Drain-Source On-State Resistance	Rds(on)	VGS=15V, ID=9A		295	355	
		VGS=20V, ID=9A, TJ=150℃		345		
DYNAMIC PARAMETERS		1				
Input Capacitance	CISS			550		pF
Output Capacitance	Coss	VDS=1000V,VGS=0V,		39		pF
Reverse Transfer Capacitance	Crss	f=1MHz,VAC=25mV		7		pF
SWITCHING PARAMETERS						
Total Gate Charge(Note2)	Q_{G}			44		nC
Gate Source Charge	Q _{GS}	VDD =800V,		4		nC
Gate Drain Charge	Q _{GD}	VGS =-3/+20 V, ID=18A		19		nC
Gate plateau voltage	V _{pl}			5		V
Turn-ON Delay Time	t _{D(ON)}			38		ns
Turn-ON Rise Time	t _R	VDS=400V, ID=18A,		68		ns
Turn-OFF Delay Time	t _{D(OFF)}	VGS = -3/+20 V ,RG=25Ω		70		ns
Turn-OFF Fall-Time	t _F			51		ns
Internal Gate Resistance	R _{G(int.)}	f =1MHz, VAC=25mV		13		Ω
SOURCE- DRAIN DIODE RATINGS		RACTERISTICS	1	1	1	1
Drain-Source Diode Forward Voltage	V _{SD}	IS=9A, VGS=-3V		6.3		V
Continuous Diode Forward Current	Is	VGS = -3V		18		Α
Reverse Recovery Time	t _{rr}	VGS = -3/+20V,IF = 18A,		30		ns
Reverse Recovery Charge	Qrr	VDS=400V,		55		nC
Peak Reverse Recovery Current	Irrm	di/dt =250A /µs		3.1		Α



BXW18M1K2H

TYPICAL CHARACTERISTICS



V_{DS} Drain-Source Voltage(v) Figure5. Typical Capacitance versus V_{DS}

Figure6. Typical Gate Charge versus V_{GS}



TYPICAL CHARACTERISTICS(Cont.)

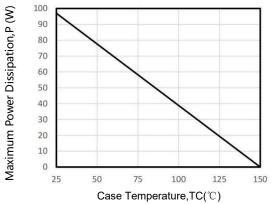
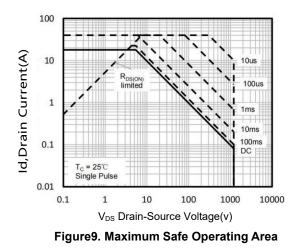


Figure7. Maximum Power Dissipation Derating versus Case Temperature



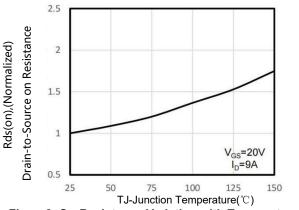


Figure8. On-Resistance Variation with Temperature

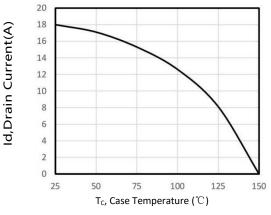


Figure10. Maximum Continuous Drain Current versus Case Temperature



Revision history

Document revision history

Date	Revision	Changes
7-Mar-2022	1.0	First release



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